# **74LVC2G38**

# Dual 2-input NAND gate; open drain

Rev. 11 — 8 April 2013

**Product data sheet** 

### 1. General description

The 74LVC2G38 provides a 2-input NAND function.

The outputs of the 74LVC2G38 devices are open-drain and can be connected to other open-drain outputs to implement active-LOW, wired-OR or active-HIGH wired-AND functions.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

### 2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant outputs for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
  - ◆ JESD8-7 (1.65 V to 1.95 V)
  - ◆ JESD8-5 (2.3 V to 2.7 V)
  - ◆ JESD8B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
  - ◆ HBM EIA/JESD22-A114F exceeds 2000 V
  - ♦ MM EIA/JESD22-A115-A exceeds 200 V
- $\pm$  24 mA output drive (V<sub>CC</sub> = 3.0 V)
- CMOS low power consumption
- Open-drain outputs
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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# 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC2G38DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74LVC2G38DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74LVC2G38GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 $\times$ 1.95 $\times$ 0.5 mm	SOT833-1
74LVC2G38GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 $\times$ 1 $\times$ 0.5 mm	SOT1089
74LVC2G38GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 $\times$ 2 $\times$ 0.5 mm	SOT996-2
74LVC2G38GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 $\times$ 1.6 $\times$ 0.5 mm	SOT902-2
74LVC2G38GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 $\times$ 1.0 $\times$ 0.35 mm	SOT1116
74LVC2G38GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203

# 4. Marking

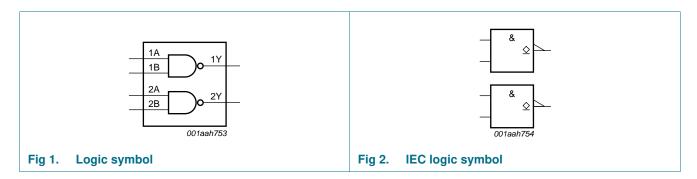
Table 2. Marking codes

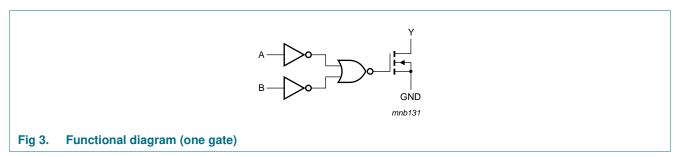
Type number	Marking code <sup>[1]</sup>
74LVC2G38DP	Y38
74LVC2G38DC	Y38
74LVC2G38GT	Y38
74LVC2G38GF	YB
74LVC2G38GD	Y38
74LVC2G38GM	Y38
74LVC2G38GN	YB
74LVC2G38GS	YB

<sup>[1]</sup> The pin 1 indicator is located on the lower left corner of the device, below the marking code.

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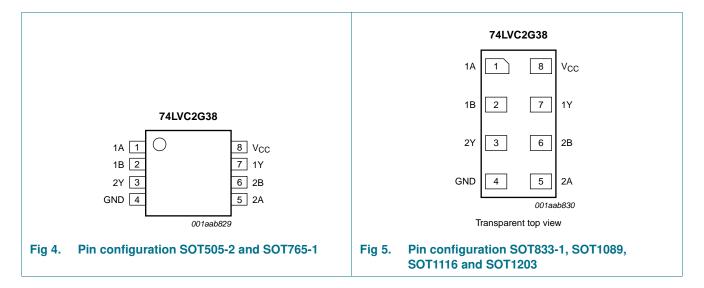
# 5. Functional diagram



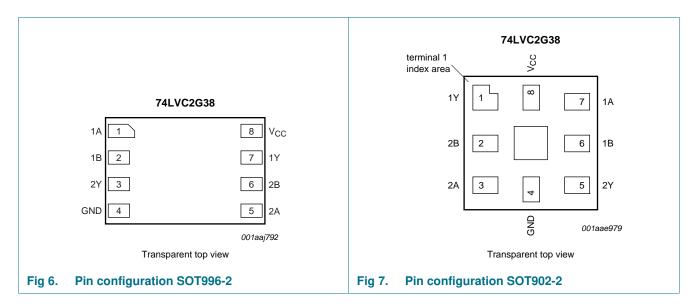


## 6. Pinning information

### 6.1 Pinning



Dual 2-input NAND gate; open drain



### 6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT505-2, SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203		
1A, 2A	1, 5	7, 3	data input
1B, 2B	2, 6	6, 2	data input
GND	4	4	ground (0 V)
1Y, 2Y	7, 3	1, 5	data output
V <sub>CC</sub>	8	8	supply voltage

# 7. Functional description

Table 4. Function table[1]

Input	Output	
nA	nB	nY
L	L	Z
L	Н	Z
Н	L	Z
Н	Н	L

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF-state.

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### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+6.5	V
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
V <sub>O</sub>	output voltage	Active mode	[1][2] -0.5	+6.5	V
		Power-down mode	[1][2] -0.5	+6.5	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
I <sub>OK</sub>	output clamping current	$V_O > V_{CC}$ or $V_O < 0 V$	-	±50	mA
Io	output current	$V_O = 0 V to V_{CC}$	-	±50	mA
I <sub>CC</sub>	supply current		-	100	mA
$I_{GND}$	ground current		-100	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	[3] _	300	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

## 9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		1.65	5.5	V
$V_{I}$	input voltage		0	5.5	V
V <sub>O</sub>	output voltage	Active mode	0	$V_{CC}$	V
		disable mode	0	5.5	V
		Power-down mode	0	5.5	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.65 \text{ V to } 2.7 \text{ V}$	-	20	ns/V
		$V_{CC} = 2.7 \text{ V to } 5.5 \text{ V}$	-	10	ns/V

<sup>[2]</sup> When  $V_{CC} = 0 \text{ V}$  (Power-down mode), the output voltage can be 5.5 V in normal operation.

<sup>[3]</sup> For TSSOP8 package: above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K.
For VSSOP8 package: above 110 °C the value of P<sub>tot</sub> derates linearly with 8 mW/K.
For XSON8 and XQFN8 packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

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### 10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = -	-40 °C to +85 °C[1]					
$V_{IH}$	HIGH-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	٧
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	-	-	٧
		V <sub>CC</sub> = 2.7 V to 3.6 V	2.0	-	-	٧
		V <sub>CC</sub> = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	٧
$V_{IL}$	LOW-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	٧
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	٧
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.8	V V V V V V V V V V V V V V V V V V V
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	$0.3 \times V_{CC}$	
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				V VCC V V V V V V V V V V V V V V V V V
		$I_O$ = 100 $\mu$ A; $V_{CC}$ = 1.65 V to 5.5 V	-	-	0.1	٧
		$I_O = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	0.08	0.45	٧
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	0.14	0.3	٧
		$I_O = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	0.19	0.4	٧
		$I_O = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	0.37	0.55	٧
		$I_O = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.43	0.55	٧
l <sub>l</sub>	input leakage current	$V_I = 5.5 \text{ V or GND}$ ; $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	±0.1	±5	μΑ
l <sub>OFF</sub>	power-off leakage current	$V_I$ or $V_O = 5.5 \text{ V}$ ; $V_{CC} = 0 \text{ V}$	-	±0.1	±10	μΑ
I <sub>CC</sub>	supply current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 1.65 V to 5.5 V; I <sub>O</sub> = 0 A	-	0.1	10	μА
Δl <sub>CC</sub>	additional supply current	per pin; $V_I = V_{CC} - 0.6 \text{ V}$ ; $I_O = 0 \text{ A}$ ; $V_{CC} = 2.3 \text{ V}$ to 5.5 V	-	5	500	μΑ
Cı	input capacitance		-	2.5	-	рF
T <sub>amb</sub> = -	-40 °C to +125 °C					
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	٧
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	-	-	٧
		V <sub>CC</sub> = 2.7 V to 3.6 V	2.0	-	-	٧
		V <sub>CC</sub> = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	V V V V V V V V V V V V V V V V V V V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	٧
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	٧
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.8	V V V V V V V V V V V V V V V V V V V
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	$0.3 \times V_{CC}$	
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O = 100 \mu A$ ; $V_{CC} = 1.65 V$ to 5.5 V	-	-	0.1	٧
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 1.65 V	-	-	0.70	V V V V V V V V V V V V V V V V V V V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	٧
		$I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.60	٧
		$I_O = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.80	V V V V V V V V V V V V V V V V V V V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.80	٧
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Table 7. Static characteristics ... continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>I</sub>	input leakage current	$V_{I}$ = 5.5 V or GND; $V_{CC}$ = 0 V to 5.5 V	-	-	±20	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_I$ or $V_O = 5.5 \text{ V}$ ; $V_{CC} = 0 \text{ V}$	-	-	±20	μΑ
I <sub>CC</sub>	supply current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}; I_O = 0 \text{ A}$	-	-	40	μА
$\Delta I_{CC}$	additional supply current	per pin; $V_I = V_{CC} - 0.6 \text{ V}$ ; $I_O = 0 \text{ A}$ ; $V_{CC} = 2.3 \text{ V}$ to 5.5 V	-	-	5000	μА

<sup>[1]</sup> All typical values are measured at  $T_{amb}$  = 25 °C.

### 11. Dynamic characteristics

## Table 8. Dynamic characteristics

Voltages are referenced to GND (ground 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		-40	°C to +85	°C	-40 °C to	o +125 °C	Unit
				Min	Typ[1]	Max	Min	Max	
$t_{PZL}$	OFF-state to LOW	nA, nB to nY; see Figure 8							
	propagation delay	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.2	3.0	8.6	1.2	10.8	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	1.8	4.8	0.7	6.0	ns
		$V_{CC} = 2.7 \text{ V}$		0.7	2.5	4.4	0.7	5.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		0.7	2.1	4.1	0.7	5.2	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.5	1.5	3.3	0.5	4.2	ns
t <sub>PLZ</sub>	LOW to OFF-state	nA, nB to nY; see Figure 8							
	propagation delay	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.2	3.0	8.6	1.2	10.8	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	1.8	4.8	0.7	6.0	ns
		$V_{CC} = 2.7 \text{ V}$		0.7	2.5	4.4	0.7	5.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		0.7	2.1	4.1	0.7	5.2	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.5	1.5	3.3	0.5	4.2	ns
$C_{PD}$	power dissipation capacitance	per gate; $V_I = GND$ to $V_{CC}$	[2]	-	5	-	-	-	pF

<sup>[1]</sup> Typical values are measured at nominal  $V_{CC}$  and at  $T_{amb}$  = 25 °C.

$$\Sigma(C_L \times V_{CC}^2 \times f_o)$$
 = sum of outputs.

<sup>[2]</sup>  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}{}^2 \times f_o)$  where:

 $f_i$  = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

 $C_L$  = output load capacitance in pF;

 $V_{CC}$  = supply voltage in V;

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### 12. Waveforms

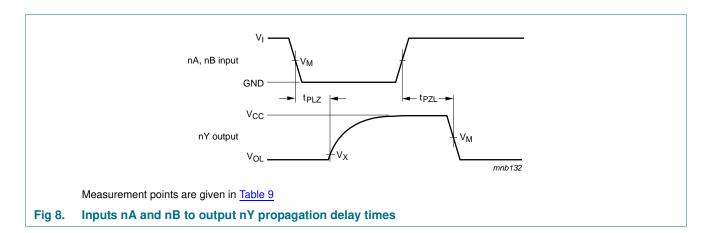
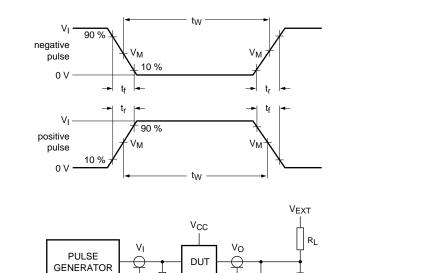


Table 9. Measurement points

Supply voltage	Input	Output				
V <sub>CC</sub>	V <sub>M</sub>	V <sub>X</sub>	V <sub>M</sub>			
1.65 V to 1.95 V	$0.5 \times V_{CC}$	V <sub>OL</sub> + 0.15 V	$0.5 \times V_{CC}$			
2.3 V to 2.7 V	$0.5 \times V_{CC}$	V <sub>OL</sub> + 0.15 V	$0.5 \times V_{CC}$			
2.7 V	1.5 V	V <sub>OL</sub> + 0.3 V	1.5 V			
3.0 V to 3.6 V	1.5 V	V <sub>OL</sub> + 0.3 V	1.5 V			
4.5 V to 5.5 V	$0.5 \times V_{CC}$	V <sub>OL</sub> + 0.3 V	$0.5 \times V_{CC}$			

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Test data is given in Table 10

Definitions for test circuit:

 $R_L$  = Load resistance.

C<sub>L</sub> = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

 $V_{EXT}$  = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input		Load		V <sub>EXT</sub>		
V <sub>CC</sub>	V <sub>I</sub>	t <sub>r</sub> , t <sub>f</sub>	C <sub>L</sub>	R <sub>L</sub>	t <sub>PLZ</sub> , t <sub>PZL</sub>		
1.65 V to 1.95 V	V <sub>CC</sub>	≤ 2.0 ns	30 pF	1 kΩ	$2 \times V_{CC}$		
2.3 V to 2.7 V	$V_{CC}$	≤ 2.0 ns	30 pF	500 Ω	$2 \times V_{CC}$		
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	6 V		
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	6 V		
4.5 V to 5.5 V	$V_{CC}$	≤ 2.5 ns	50 pF	500 Ω	$2 \times V_{CC}$		

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### 13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

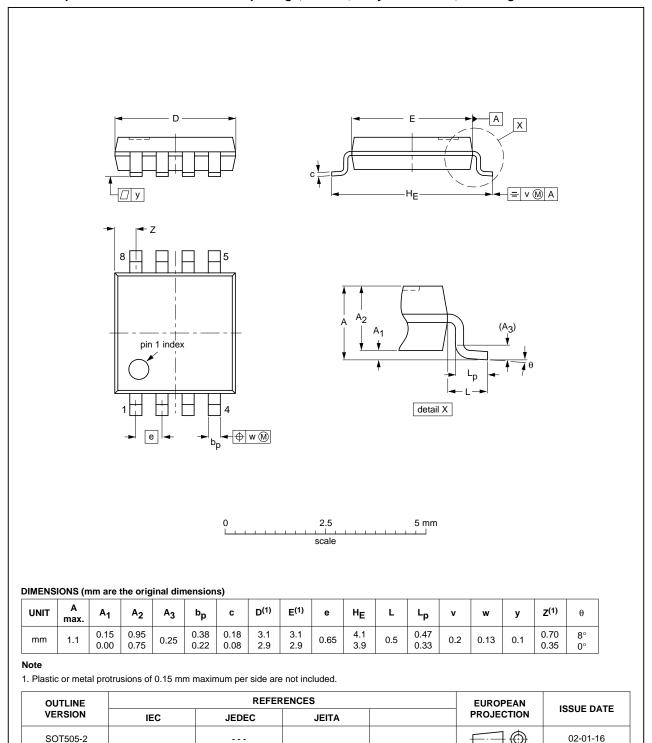
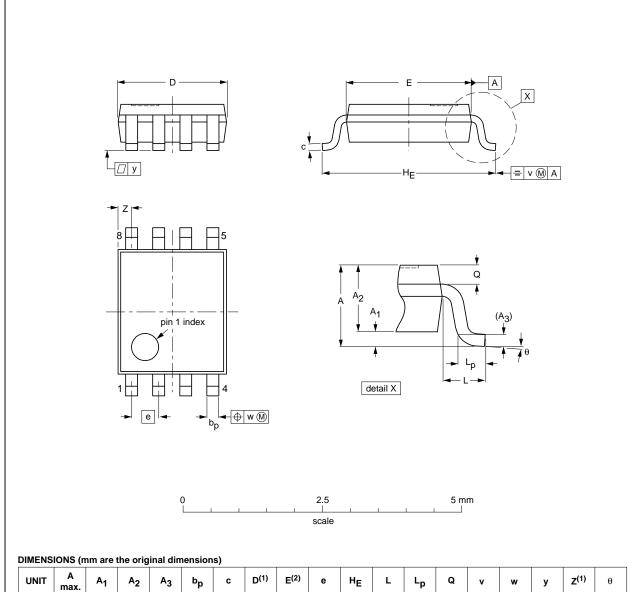


Fig 10. Package outline SOT505-2 (TSSOP8)

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#### VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	А3	bp	С	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

#### Notes

- Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT765-1		MO-187				02-06-07	

Fig 11. Package outline SOT765-1 (VSSOP8)

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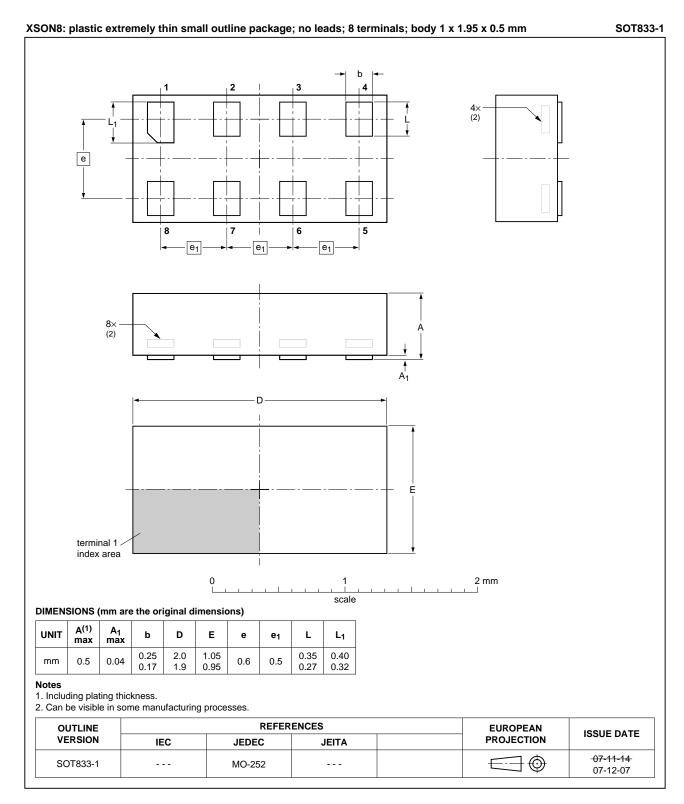


Fig 12. Package outline SOT833-1 (XSON8)

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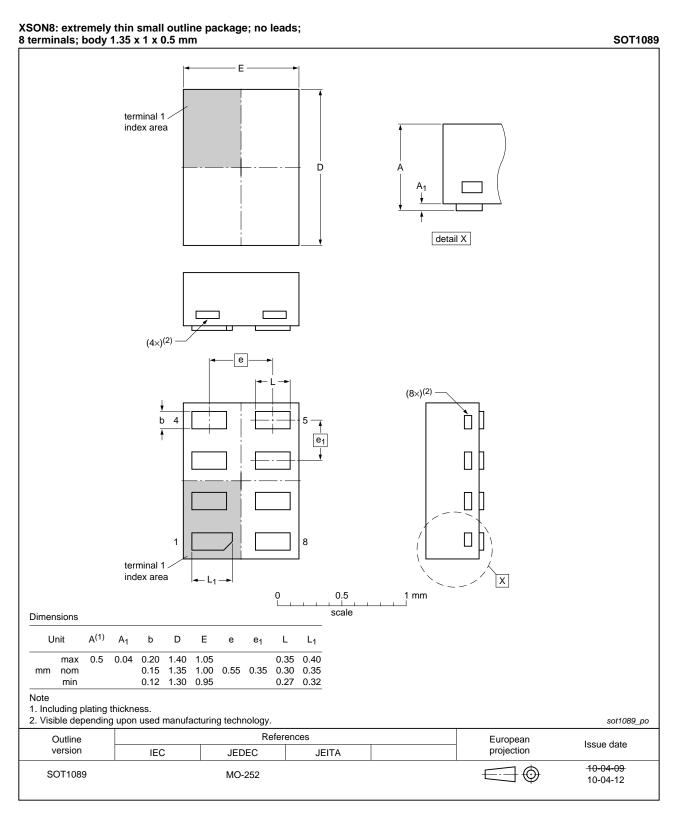


Fig 13. Package outline SOT1089 (XSON8)

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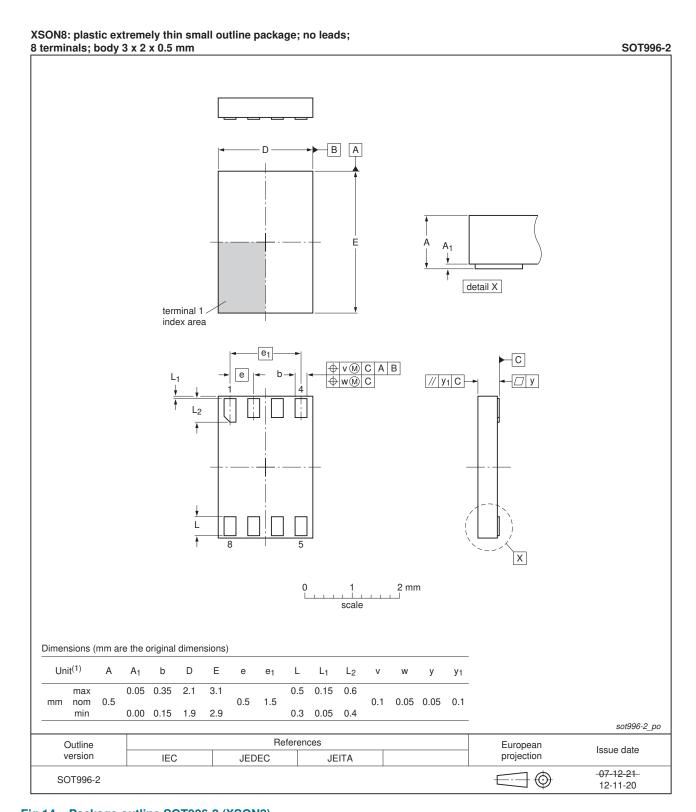


Fig 14. Package outline SOT996-2 (XSON8)

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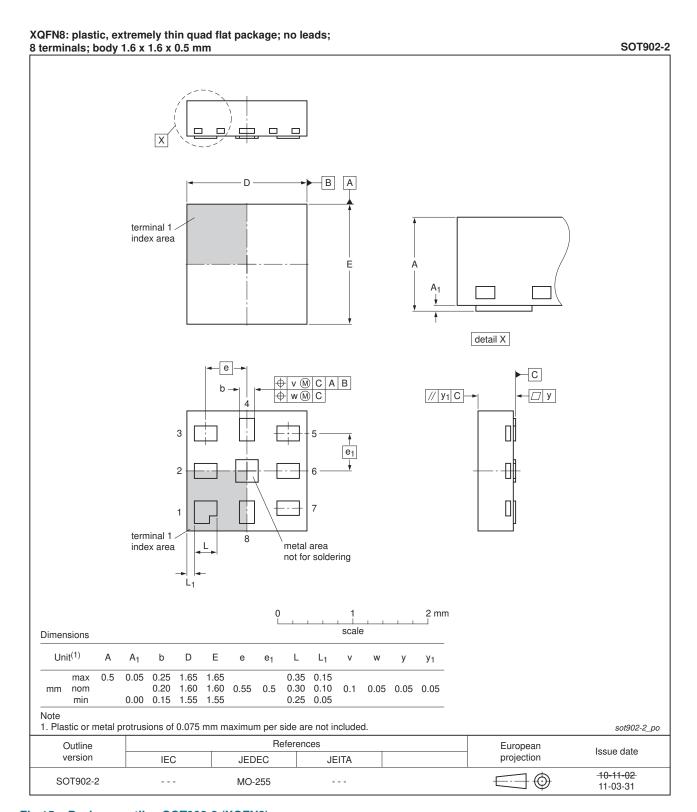


Fig 15. Package outline SOT902-2 (XQFN8)

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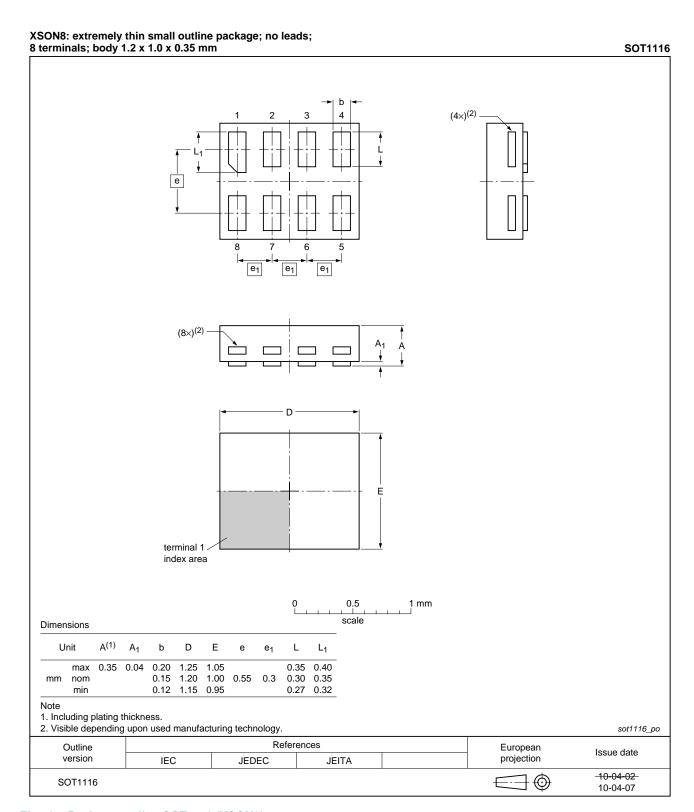


Fig 16. Package outline SOT1116 (XSON8)

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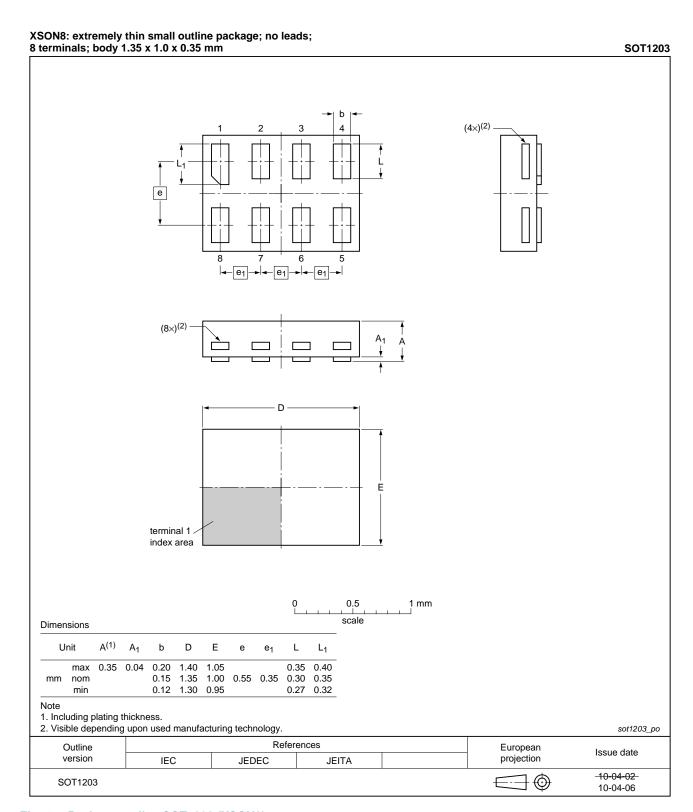


Fig 17. Package outline SOT1203 (XSON8)

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74LVC2G38 **NXP Semiconductors** 

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### 14. Abbreviations

#### Table 11. Abbreviations

Acronym	Description	
CMOS	Complementary Metal-Oxide Semiconductor	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
MM	Machine Model	
TTL	Transistor-Transistor Logic	

# 15. Revision history

#### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC2G38 v.11	20130408	Product data sheet	-	74LVC2G38 v.10
Modifications:	<ul> <li>For type nu</li> </ul>	mber 74LVC2G38GD XSO	N8U has changed to XS	SON8.
74LVC2G38 v.10	20120628	Product data sheet	-	74LVC2G38 v.9
Modifications:	<ul> <li>For type nu</li> </ul>	mber 74LVC2G38GM the S	SOT code has changed	to SOT902-2.
74LVC2G38 v.9	20111128	Product data sheet	-	74LVC2G38 v.8
Modifications:	<ul> <li>Legal pages</li> </ul>	s updated.		
74LVC2G38 v.8	20101104	Product data sheet	-	74LVC2G38 v.7
74LVC2G38 v.7	20090320	Product data sheet	-	74LVC2G38 v.6
74LVC2G38 v.6	20080219	Product data sheet	-	74LVC2G38 v.5
74LVC2G38 v.5	20070904	Product data sheet	-	74LVC2G38 v.4
74LVC2G38 v.4	20060516	Product data sheet	-	74LVC2G38 v.3
74LVC2G38 v.3	20050201	Product specification	-	74LVC2G38 v.2
74LVC2G38 v.2	20041018	Product specification	-	74LVC2G38 v.1
74LVC2G38 v.1	20031027	Product specification	-	-

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### 16. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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